Phase Control Thyristors (Hockey PUK Version), 720 A

TO-200AB (E-PUK)

FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case TO-200AB (E-PUK)
- Lead (Pb)-free
- Designed and qualified for industrial level

Pb-free
RoHS COMPLIANT

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

PRODUCT SUMMARY	
$I_{T(AV)}$	720 A

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		720	A
	T_{hs}	55	°C
$I_{T(RMS)}$		1420	A
	T_{hs}	25	°C
I_{TSM}	50 Hz	9000	A
	60 Hz	9420	
I^2t	50 Hz	405	kA^2s
	60 Hz	370	
V_{DRM}/V_{RRM}		400 to 1600	V
t_q	Typical	100	µs
T_J		- 40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM}, MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM}, MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
ST330C..C	04	400	500	50
	08	800	900	
	12	1200	1300	
	14	1400	1500	
	16	1600	1700	

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at heatsink temperature	$I_{T(AV)}$	180° conduction, half sine wave double side (single side) cooled			720 (350)	A
					55 (75)	°C
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 25 °C heatsink temperature double side cooled			1420	A
Maximum peak, one-cycle non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	9000	
		t = 8.3 ms			9420	
		t = 10 ms	100 % V_{RRM} reapplied		7570	
		t = 8.3 ms			7920	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied		405	kA^2s
		t = 8.3 ms			370	
		t = 10 ms	100 % V_{RRM} reapplied		287	
		t = 8.3 ms			262	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied			4050	$kA^2\sqrt{s}$
Low level value of threshold voltage	$V_{T(TO)1}$	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.91	V
High level value of threshold voltage	$V_{T(TO)2}$	(I > π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.92	
Low level value of on-state slope resistance	r_{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.58	mΩ
High level value of on-state slope resistance	r_{t2}	(I > π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.57	
Maximum on-state voltage	V_{TM}	I_{pk} = 1810 A, $T_J = T_J$ maximum, t_p = 10 ms sine pulse			1.96	V
Maximum holding current	I_H	T_J = 25 °C, anode supply 12 V resistive load			600	mA
Typical latching current	I_L				1000	

SWITCHING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dI/dt	Gate drive 20 V, 20 Ω, $t_r \leq 1$ µs $T_J = T_J$ maximum, anode voltage ≤ 80 % V_{DRM}	1000	A/µs
Typical delay time	t_d	Gate current 1 A, dI_g/dt = 1 A/µs V_d = 0.67 % V_{DRM}, T_J = 25 °C	1.0	µs
Typical turn-off time	t_q	I_{TM} = 550 A, $T_J = T_J$ maximum, dI/dt = 40 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 Ω, t_p = 500 µs	100	

BLOCKING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I_{RRM}, I_{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	50	mA

TRIGGERING

PARAMETER	SYMBOL	TEST CONDITIONS		VALUES TYP.	VALUES MAX.	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		10.0		W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, f = 50 Hz, d% = 50		2.0		W
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		3.0		A
Maximum peak positive gate voltage	$+ V_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms		20		V
Maximum peak negative gate voltage	$- V_{GM}$			5.0		V
DC gate current required to trigger	I_{GT}	T_J = - 40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	200	-	mA
		T_J = 25 °C		100	200	mA
		T_J = 125 °C		50	-	mA
DC gate voltage required to trigger	V_{GT}	T_J = - 40 °C		2.5	-	V
		T_J = 25 °C		1.8	3.0	V
		T_J = 125 °C		1.1	-	V
DC gate current not to trigger	I_{GD}	$T_J = T_J$ maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V_{DRM} anode to cathode applied	10		mA
DC gate voltage not to trigger	V_{GD}			0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction temperature range	T_J		- 40 to 125	°C
Maximum storage temperature range	T_{Stg}		- 40 to 150	°C
Maximum thermal resistance, junction to heatsink	R_{thJ-hs}	DC operation single side cooled	0.09	K/W
		DC operation double side cooled	0.04	K/W
Maximum thermal resistance, case to heatsink	R_{thC-hs}	DC operation single side cooled	0.02	K/W
		DC operation double side cooled	0.01	K/W
Mounting force, ± 10 %			9800 (1000)	N (kg)
Approximate weight			83	g
Case style		See dimensions - link at the end of datasheet	TO-200AB (E-PUK)	

ΔR_{thJ-hs} CONDUCTION

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.012	0.011	0.008	0.007	$T_J = T_J$ maximum	K/W
120°	0.014	0.012	0.014	0.013		
90°	0.017	0.015	0.019	0.017		
60°	0.025	0.022	0.026	0.023		
30°	0.043	0.036	0.043	0.037		

Note

- The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

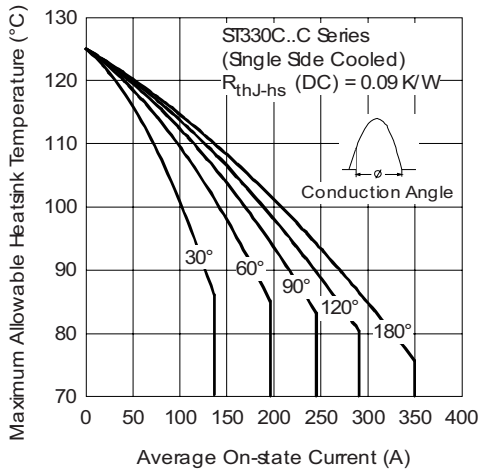

Fig. 1 - Current Ratings Characteristics

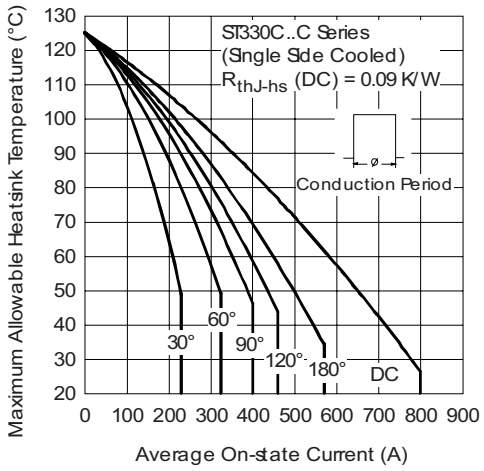

Fig. 2 - Current Ratings Characteristics

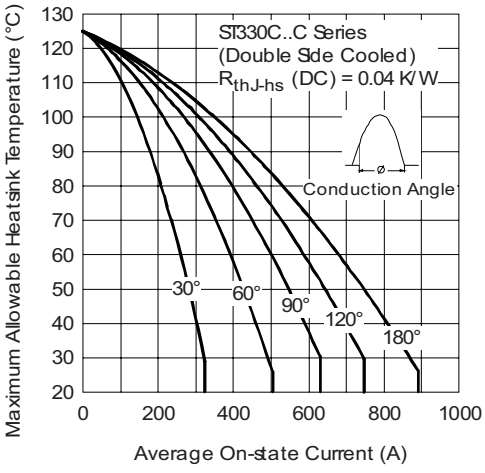

Fig. 3 - Current Ratings Characteristics

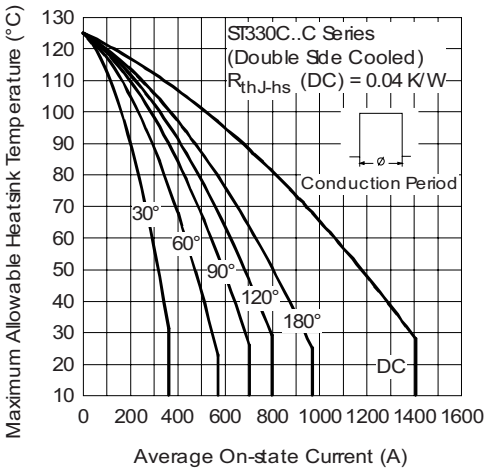

Fig. 4 - Current Ratings Characteristics

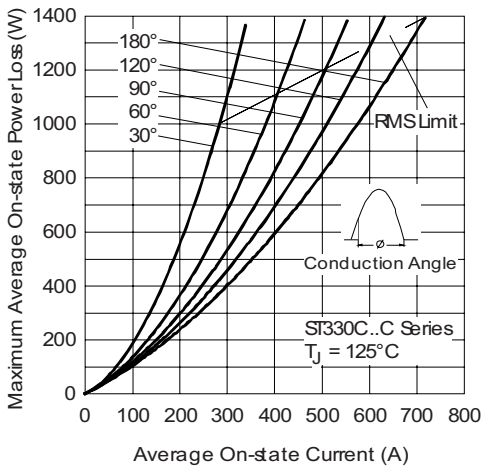

Fig. 5 - On-State Power Loss Characteristics

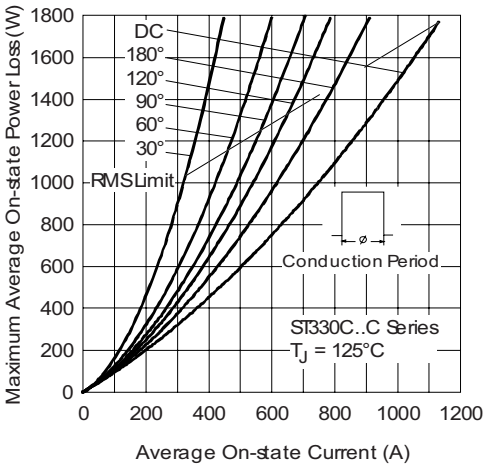

Fig. 6 - On-State Power Loss Characteristics

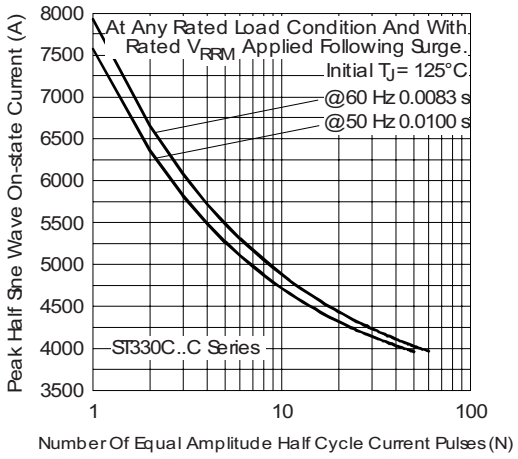

Fig. 7 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

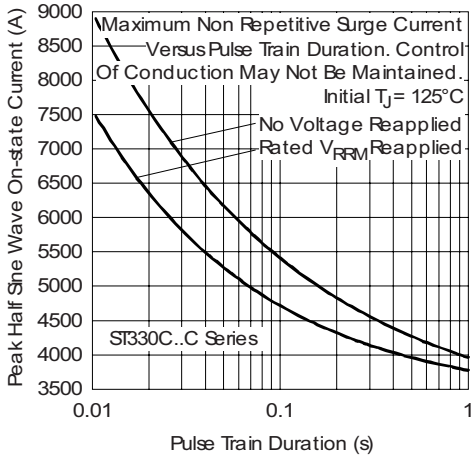

Fig. 8 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

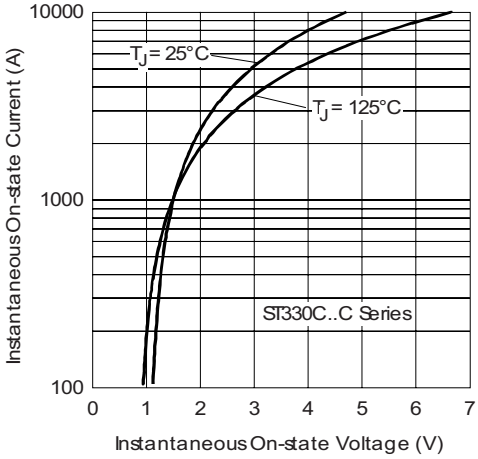

Fig. 9 - On-State Voltage Drop Characteristics

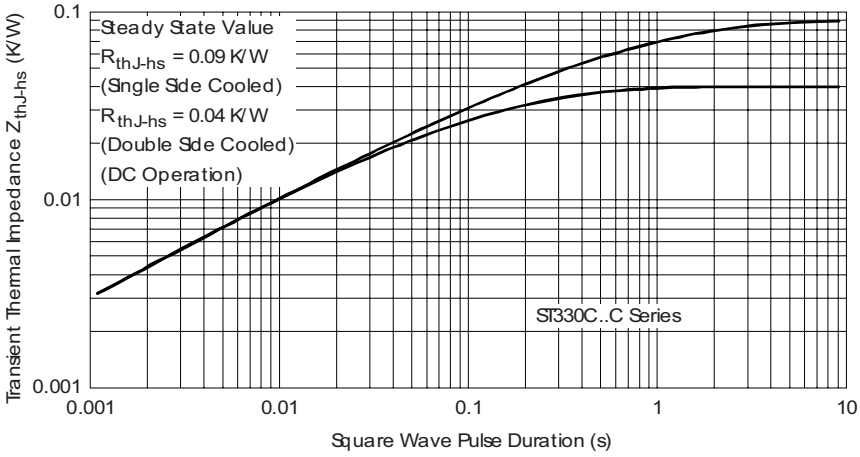

Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

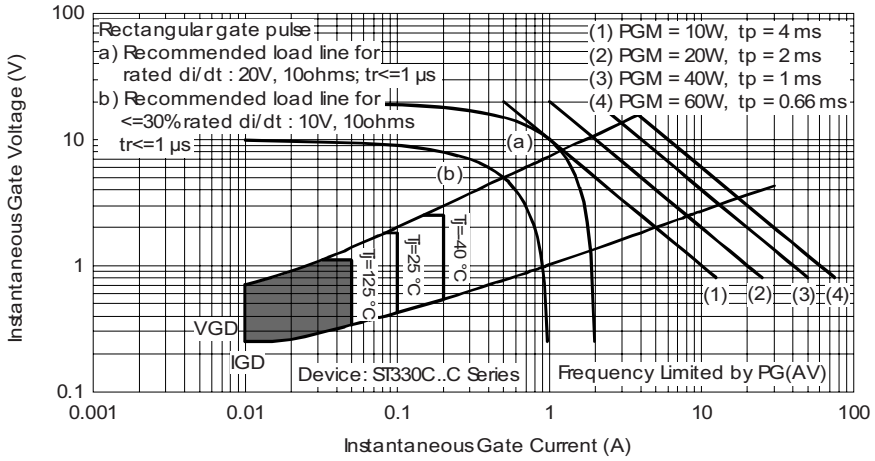

Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code

ST	33	0	C	16	C	1	-	PbF
1	2	3	4	5	6	7	8	9

- **1** - Thyristor
- **2** - Essential part number
- **3** - 0 = Converter grade
- **4** - C = Ceramic PUK
- **5** - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- **6** - C = PUK case TO-200AB (E-PUK)
- **7** - 0 = Eyelet terminals (gate and auxiliary cathode unsoldered leads)
  1 = Fast-on terminals (gate and auxiliary cathode unsoldered leads)
  2 = Eyelet terminals (gate and auxiliary cathode soldered leads)
  3 = Fast-on terminals (gate and auxiliary cathode soldered leads)
- **8** - Critical dV/dt: • None = 500 V/µs (standard selection)
  • L = 1000 V/µs (special selection)
- **9** - Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95075

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